

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	21	arena near chantal.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	3	italiano near joe.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	0	brabat near paul.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	6	brabant near paul.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	22981	(substrate) near25 (elevat\$3 or esd)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	21178	(substrate) near25 (elevat\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	661	(substrate) near25 (elevat\$3) near25 (etch\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	21	(substrate) near25 (elevat\$3) near25 (etch\$3) near25 (epitaxial)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	17	(substrate) near25 (polycrystal\$3) near25 (etch\$3) near25 (epitaxial)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	3	(wafer) near25 (polycrystal\$3) near25 (etch\$3) near25 (epitaxial)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	0	(elevat\$3) near25 (polycrystal\$3) near25 (etch\$3) near25 (epitaxial)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	38	(polycrystal\$3) near25 (etch\$3) near25 (epitaxial)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	17	(polycrystal\$3) near25 (gate near electrode) near25 (epitaxial)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	69	(polycrystal\$3) near25 (gate or electrode) near25 (epitaxial)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L15	193	(polycrystal\$3) near35 (substrate) near25 (epitaxial)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L16	11	(poly-crystal\$3) near35 (substrate) near25 (epitaxial)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
17	BRS	L17	16	(poly near crystal\$3) near35 (substrate) near25 (epitaxial)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
18	BRS	L18	454	(polycrystal\$3) near25 (epitaxial)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
19	BRS	L19	35	(poly-crystal\$3) near25 (epitaxial)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
20	BRS	L20	58	(poly near crystal\$3) near25 (epitaxial)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
21	BRS	L21	3467	(polysilicon) near25 (epitaxial)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
22	BRS	L22	582	(polysilicon) near25 (epitaxial) near25 (etch\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
23	BRS	L23	116	(poly\$3) near25 (epitaxial) near25 (etch\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
24	BRS	L24	87	(poly) near25 (epitaxial) near25 (etch\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
25	BRS	L25	0	(poly) near25 (epitaxial) near25 (flash near etch\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
26	BRS	L26	9587	(poly) near25 (etch\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
27	BRS	L27	740	(gate near electrode) near15 (poly) near25 (etch\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
28	BRS	L29	29	((gate near electrode) near15 (polycrystal\$3) near25 (etch\$3)) and repeat\$3	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
29	BRS	L28	242	(gate near electrode) near15 (polycrystal\$3) near25 (etch\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B



	U	1	Document ID	Title
1			US 20030205731 A1	Semiconductor integrated circuit device and manufacturing method thereof
2			US 20020173091 A1	Semiconductor integrated circuit device and manufacturing method thereof
3			US 20010046766 A1	Semiconductor devices and methods for manufacturing the same
4			US 20010023108 A1	Semiconductor apparatus having elevated source and drain structure and manufacturing method therefor
5			US 6815761 B2	Semiconductor integrated circuit device
6			US 6583467 B2	Semiconductor integrated circuit device

	U	1	Document ID	Title
7			US 6444514 B1	Semiconductor integrated circuit device and manufacturing method thereof
8			US 6335251 B1	Semiconductor apparatus having elevated source and drain structure and manufacturing method therefor
9			US 6232641 B1	Semiconductor apparatus having elevated source and drain structure and manufacturing method therefor
10			US 5055905 A	Semiconductor device
11			US 4353085 A	Integrated semiconductor device having insulated gate field effect transistors with a buried insulating film
12			JP 03060041 A	MANUFACTURE OF FIELD EFFECT TRANSISTOR
13	X		JP 63155764 A	MANUFACTURE OF MOS TRANSISTOR
14	X		JP 54159185 A	SEMICONDUCTOR DEVICE
15	X		JP 06310725 A	Insulated gate type bipolar transistor prodn. - involves formation of emitter - auxiliary electrode layer with silicide layer between emitter domain difference layer and emitter electrode

	U	1	Document ID	Title
16	X		JP 06236967 A	Semiconductor device fabrication method used in VLSI circuit prodn. - incorporates polycrystal silicon doped with arsenic above silicon epitaxial layer through gate oxide film before gate electrode formation
17	X		JP 55056646 A	CMOS integrated circuit mfr. - includes forming phosphorus-silicate glass layer which is heated to diffuse phosphorus into gate electrodes